L Number	Hits	Search Text	DB	Time stamp
1	178	have has having	USPAT	2003/09/23 11:28
2	1431	silicon adj sapphire	USPAT	2003/09/23 11:28
3	14	(silicon adj sapphire) with (advantage benefit better)	USPAT	2003/09/23 13:14
4	18685	gallium adj arsenide	USPAT	2003/09/23 11:32
5	308	(gallium adj arsenide) with (advantage benefit better)	USPAT	2003/09/23 12:10
6	28708	germanium	USPAT	2003/09/23 12:10
7	442	germanium with (advantage benefit better)	USPAT	2003/09/23 12:17
8	1	("6143072").PN.	USPAT:	2003/09/23 12:17
ا	•	(0143072).FN.		2003/09/23 12.17
9	1	("5994985").PN.	US-PGPUB	2003/09/23 12:23
ا		(3994903).FN.	USPAT;	2003/09/23 12.23
10	1	("400CE04") DN	US-PGPUB	0000/00/00 40 44
10	ı	("4906594").PN.	USPAT;	2003/09/23 13:14
1	0007		US-PGPUB	
11	8067	thermal adj oxide	USPAT;	2003/09/23 16:26
1.0			US-PGPUB	
12	107	(thermal adj oxide) with (advantage benefit better)	USPAT	2003/09/23 14:16
13	1898	(thermal adj oxide) with gate	USPAT;	2003/09/23 13:31
			US-PGPUB	
14	0	((thermal adj oxide) with gate) same for	USPAT;	2003/09/23 13:30
			US-PGPUB	
15	1078	((thermal adj oxide) with gate) same substrate	USPAT;	2003/09/23 13:31
			US-PGPUB	
16	827	((thermal adj oxide) with gate) same substrate	USPAT	2003/09/23 13:31
17	0	(("6143072").PN.) same transistor	USPAT	2003/09/23 13:31
18	232	(((thermal adj oxide) with gate) same substrate) same	USPAT	2003/09/23 13:32
] .	202	transistor	001 71	2003/03/23 13.32
19	269	(thermal adj oxide) with (advantage benefit better improv\$3)	USPAT	2003/09/23 13:46
20	162	((thermal adj oxide) with (advantage benefit better improv\$3)	USPAT	2003/09/23 13:46
20	102	not ((thermal adj oxide) with (advantage benefit better))	USPAI	2003/09/23 13.46
21	0	gate adj oxide same thermal adj oxxide	LICDAT	2002/00/22 44:40
22	897	gate adj oxide same thermal adj oxide	USPAT	2003/09/23 14:16
23	097		USPAT	2003/09/23 16:22
ا کی	1	("20020030539").PN.	USPAT;	2003/09/23 14:46
24	200	thormal adi avida with (hattas bissas a tara a tara a tara	US-PGPUB	0000000000
	368	thermal adj oxide with (better higher improv\$3)	USPAT	2003/09/23 14:48
25	39	thermal adj oxide near3 purpose	USPAT	2003/09/23 16:20
26	664	silicon adj (oxide near dioxide)	USPAT	2003/09/23 16:21
27	0	(silicon adj (oxide near dioxide)) with (benefit better	USPAT	2003/09/23 16:21
		advantage improv\$3)		
28	1	("4868619").PN.	USPAT;	2003/09/23 16:24
.			US-PGPUB	
29	409	11.ab.	USPAT;	2003/09/23 16:26
			US-PGPUB	
30	307	11.ab. and (transistor FET MOSFET CMOS)	USPAT:	2003/09/23 16:27
		·	US-PGPUB	
31	13	11.ti.	USPAT:	2003/09/23 17:13
			US-PGPUB	
32	1	("6143072").PN.	USPAT:	2003/09/23 17:13
	·		US-PGPUB	2003/03/23 17.13
			L OS-FGFUB	L